





TRSF3222E SLLS823A - JULY 2007 - REVISED AUGUST 2021

# 3-V to 5.5-V Multichannel RS-232 Line Driver and Receiver with ±15-kV ESD Protection

#### 1 Features

- ESD Protection for RS-232 bus pins
  - ±15-kV Human-body model (HBM)
  - ±8-kV IEC 61000-4-2, Contact discharge
  - ±15-kV IEC 61000-4-2, Air-gap discharge
- Meets or exceeds the requirements of TIA/ EIA-232-F and ITU v.28 standards
- Operates with 3-V to 5.5-V V<sub>CC</sub> supply
- Operates up to 1000 kbit/s
- Two drivers and two receivers
- Low standby current . . . 1 µA Typ
- External capacitors . . . 4 × 0.1 µF
- Accepts 5-V logic input with 3.3-V supply

# 2 Applications

- **Industrial PCs**
- Wired networking
- Data center and networking equipment
- **Notebooks**
- Hand-held equipment

# 3 Description

The TRSF3222E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND).

The TRSF3222E meets the requirements of TIA/ EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The TRSF3222E operates at typical data signaling rates up to

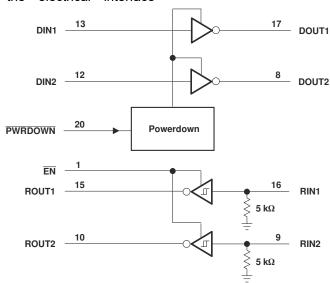
1000 kbit/s and is an improved drop-in replacement for industry-popular '3222 two-driver, two-receiver functions.

The TRSF3222E can be placed in the power-down mode by setting the power-down (PWRDOWN) input low, which draws only 1 µA from the power supply. When the device is powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V<sub>CC</sub>, and V- is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable ( EN) high.

#### **Device Information**

| PART NUMBER | PACKAGE <sup>(1)</sup> | BODY SIZE (NOM)   |
|-------------|------------------------|-------------------|
|             | DB (SSOP) (20)         | 10.2 mm x 5.30 mm |
| TRSF3222E   | DW (SOIC) (20)         | 15.4 mm x 7.50 mm |
|             | PW (TSSOP) (20)        | 7.80 mm v 4.40 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Pin numbers shown are for the DB, DW, and PW packages.

### Logic Diagram (Positive Logic)



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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

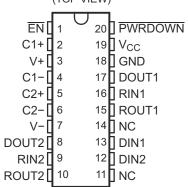
| С | hanges from Revision * (July 2007) to Revision A (August 2021)   | Page           |
|---|--|----------------|
| • | Updated the list of Applications   | 1              |
|   | Deleted the Ordering Information table   |                |
|   | Added the Device Information table, the Pin Configuration and Functions, the Detailed Description sect         |                |
|   | the Application and Implementation section   | 1              |
| • | Deleted the Package thermal impedance from the Absolute Maximum Ratings  | 4              |
| • | Added the ESD Ratings table  | 4              |
| • | Added the ESD Ratings - IEC Specifications table   | 4              |
| • | Added the Thermal Information table  | <mark>5</mark> |
|   | Changed the value of R <sub>θJA</sub> for PW package (previously in the Absolute Maximum Ratings table), and a |                |
|   | additional thermal parameters for all packages in the Thermal Information table                                | <mark>5</mark> |

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# **5 Pin Configuration and Functions**

DB, DW, OR PW PACKAGE (TOP VIEW)



NC - No internal connection

Table 5-1. Pin Functions

| PIN I/O         |       | 1/0 | DESCRIPTION                 |
|-----------------|-------|-----|-----------------------------|
| NAME            | NO.   | 1/0 | DESCRIPTION                 |
| C1+             | 2     | _   | Charge pump capacitor pin   |
| C1-             | 4     | _   | Charge pump capacitor pin   |
| C2+             | 5     | _   | Charge pump capacitor pin   |
| C2-             | 6     | _   | Charge pump capacitor pin   |
| DIN1            | 13    | I   | Driver logic input          |
| DIN2            | 12    | I   | Driver logic input          |
| DOUT1           | 17    | 0   | RS-232 driver output        |
| DOUT2           | 8     | 0   | RS-232 driver output        |
| EN              | 1     | I   | Receiver enable, active low |
| GND             | 18    | _   | Ground                      |
| NC              | 11,14 | _   | No internal connection      |
| PWRDOWN         | 20    | I   | Driver disable, active low  |
| RIN1            | 16    | I   | RS-232 receiver input       |
| RIN2            | 9     | I   | RS-232 receiver input       |
| ROUT1           | 15    | 0   | Receiver logic output       |
| ROUT2           | 10    | 0   | Receiver logic output       |
| V <sub>CC</sub> | 19    | _   | Power Supply                |
| V+              | 3     | _   | Charge pump capacitor pin   |
| V-              | 7     | _   | Charge pump capacitor pin   |



# **6 Specifications**

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

|                  |   |                       | MIN   | MAX                   | UNIT |
|------------------|---|-----------------------|-------|-----------------------|------|
| V <sub>CC</sub>  | Supply voltage range <sup>(2)</sup>                 |                       | -0.3  | 6                     | V    |
| V+               | Positive-output supply voltage range <sup>(2)</sup> |                       | -0.3  | 7                     | V    |
| V-               | Negative-output supply voltage range <sup>(2)</sup> |                       | 0.3   | -7                    | V    |
| V+ – V–          | Supply voltage difference <sup>(2)</sup>            |                       |       | 13                    | V    |
| Vı               | Input voltage range                                 | Driver ( EN, PWRDOWN) | -0.3  | 6                     | V    |
|                  |   | Receiver              | -25   | 25                    | V    |
| V                | Output valtage renge                                | Driver                | -13.2 | 13.2                  | V    |
| V <sub>O</sub>   | Output voltage range                                | Receiver              | -0.3  | V <sub>CC</sub> + 0.3 | V    |
| TJ               | Operating virtual junction temperature              |                       |       | 150                   | °C   |
| T <sub>stg</sub> | Storage temperature range                           |                       | -65   | 150                   | °C   |

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

# 6.2 ESD Ratings

|         |                      |                                   |  | VALUE   | UNIT |
|---------|----------------------|-----------------------------------|--|---------|------|
| V (EOD) |                      | Human-body model (HBM), per ANSI/ | All pins except RIN1, RIN2, DOUT1 and DOUT2 pins | ±3000   |      |
|         | ESDA/IEDEC IS 001(1) | ESDA/JEDEC JS-001 <sup>(1)</sup>  | RIN1, RIN2, DIN1 and DOUT2 pins to GND           | ±15,000 | V    |
|         |                      |                                   | ±1500  |         |      |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 ESD Ratings - IEC Specifications

|                    |                      |            |                                     |                                    | VALUE   | UNIT     |
|--------------------|----------------------|------------|-------------------------------------|------------------------------------|---------|----------|
| V <sub>(ESD)</sub> |                      | ctrostatic | IEC 61000-4-2 Contact Discharge (1) | Pins RIN1, RIN2, DOUT1, DOUT2 only | ±8,000  | V        |
| \ \ \ (E           | <sup>(SD)</sup> disc | harge      | IEC 61000-4-2 Air Discharge (1)     |                                    | ±15,000 | <b>'</b> |

(1) For PW package only, a minimum of 1-µF capacitor is required between V<sub>CC</sub> and GND to meet the specified IEC 61000-4-2 rating.

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<sup>(2)</sup> All voltages are with respect to network GND.



# **6.4 Recommended Operating Conditions**

See Figure 9-1 and (1)

|                 |  |                       |                         | MIN | NOM | MAX | UNIT |
|-----------------|--|-----------------------|-------------------------|-----|-----|-----|------|
|                 | Supply voltage   |                       | V <sub>CC</sub> = 3.3 V | 3   | 3.3 | 3.6 | V    |
|                 |  |                       | V <sub>CC</sub> = 5 V   | 4.5 | 5   | 5.5 | ·    |
| V               | Driver and control high-level input voltage IDIN_EN_PWRD()WN | DIN EN DWPDOWN        | V <sub>CC</sub> = 3.3 V | 2   |     |     | V    |
| V <sub>IH</sub> |  | V <sub>CC</sub> = 5 V | 2.4                     |     |     | ·   |      |
| V <sub>IL</sub> | Driver and control low-level input voltage                   | DIN, EN, PWRDOWN      |                         |     |     | 0.8 | V    |
| VI              | Driver and control input voltage                             | DIN, EN, PWRDOWN      |                         | 0   |     | 5.5 | V    |
| VI              | Receiver input voltage                                       |                       |                         | -25 |     | 25  | V    |
| т               |  |                       | TRSF3222EC              | 0   |     | 70  | °C   |
| T <sub>A</sub>  | Operating free-air temperature                               | TRSF3222EI            | -40                     |     | 85  |     |      |

<sup>(1)</sup> Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

#### 6.5 Thermal Information

| THERMAL METRIC(1)                            |   | DW (SOIC)   | PW (TSSOP)                                 | UNIT   |
|--|---|---|--|--|
|  | 20 Pins   | 20 Pins   | 20 Pins                                    |  |
| Junction-to-ambient thermal resistance       | 70  | 58  | 94.1                                       | °C/W   |
| Junction-to-board thermal resistance         | 33.6  | 30.0  | 35.2                                       | °C/W   |
| Junction-to-top characterization parameter   | 36.4  | 29.6  | 45.5                                       | °C/W   |
| Junction-to-board characterization parameter | 4.8   | 7.7   | 3.1  | °C/W   |
| Junction-to-case (bottom) thermal resistance | 35.9  | 29.3  | 45.1                                       | °C/W   |
|  | Junction-to-ambient thermal resistance  Junction-to-board thermal resistance  Junction-to-top characterization parameter  Junction-to-board characterization parameter  Junction-to-case (bottom) thermal | Junction-to-ambient thermal resistance 70  Junction-to-board thermal resistance 33.6  Junction-to-top characterization parameter 36.4  Junction-to-board characterization 4.8  parameter Junction-to-case (bottom) thermal 35.9 | 20 Pins   20 Pins   20 Pins   20 Pins   58 | THERMAL METRIC(1)         DB (SSOP)         DW (SOIC)         PW (TSSOP)           20 Pins         20 Pins         20 Pins           Junction-to-ambient thermal resistance         70         58         94.1           Junction-to-board thermal resistance         33.6         30.0         35.2           Junction-to-top characterization parameter         36.4         29.6         45.5           Junction-to-board characterization parameter         4.8         7.7         3.1           Junction-to-case (bottom) thermal         35.9         29.3         45.1 |

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

#### 6.6 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

|                | PARAMETER                            | TEST CONDITIONS <sup>(2)</sup>      | MIN TYP <sup>(1)</sup> | MAX | UNIT |
|----------------|--------------------------------------|-------------------------------------|------------------------|-----|------|
| I <sub>1</sub> | Input leakage current ( EN, PWRDOWN) |                                     | ±0.01                  | ±1  | μΑ   |
| I              | Supply current                       | No load, PWRDOWN at V <sub>CC</sub> | 0.3                    | 1   | mA   |
| Icc            | Supply current (powered off)         | No load, PWRDOWN at GND             | 1                      | 10  | μΑ   |

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

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<sup>(2)</sup> Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.



#### 6.7 Electrical Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

| PARAMETER       |   | TEST CONDITIONS <sup>(3)</sup>            |   |     | TYP <sup>(1)</sup> | MAX | UNIT |
|-----------------|---|---|---|-----|--------------------|-----|------|
| V <sub>OH</sub> | High-level output voltage                   | DOUT at $R_L = 3 \text{ k}\Omega$ to GND, | DIN = GND   | 5   | 5.4                |     | V    |
| V <sub>OL</sub> | Low-level output voltage                    | DOUT at $R_L = 3 \text{ k}\Omega$ to GND, | DIN = V <sub>CC</sub>   | -5  | -5.4               |     | V    |
| I <sub>IH</sub> | High-level input current                    | V <sub>I</sub> = V <sub>CC</sub>          |   |     | ±0.01              | ±1  | μΑ   |
| I <sub>IL</sub> | Low-level input current                     | V <sub>I</sub> at GND                     | / <sub>I</sub> at GND   |     | ±0.01              | ±1  | μΑ   |
|                 | Chart singuit autout accompat(2)            | V <sub>CC</sub> = 3.6 V                   | V <sub>O</sub> = 0 V  |     | ±35                | ±60 | mA   |
| los             | Short-circuit output current <sup>(2)</sup> | V <sub>CC</sub> = 5.5 V                   | V <sub>O</sub> = 0 V  |     | ±35                | ±00 | IIIA |
| r <sub>o</sub>  | Output resistance                           | V <sub>CC</sub> , V+, and V- = 0 V,       | V <sub>O</sub> = ±2 V   | 300 | 10M                |     | Ω    |
|                 | Output leakens aurrent                      | DWDDOWN - CND                             | V <sub>CC</sub> = 3 V to 3.6 V,<br>V <sub>O</sub> = ±12 V                 |     |                    | ±25 |      |
| loz             | Output leakage current                      | Output leakage current PWRDOWN = GND      | $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V},$<br>$V_{O} = \pm 10 \text{ V}$ |     |                    | ±25 | μA   |

- All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
- Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V  $\pm$  0.5 V.

## 6.8 Switching Characteristics: Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

|   | PARAMETER                          |                                     | TEST CONDITIONS(3)                      |                                    |      | TYP <sup>(1)</sup> | MAX | UNIT   |  |
|---|------------------------------------|-------------------------------------|---|------------------------------------|------|--------------------|-----|--------|--|
|   |                                    |                                     | C <sub>L</sub> = 1000 pF                |                                    | 250  |                    |     |        |  |
|   | Maximum data rate (See Figure 7-1) | See Figure 7-1) One DOUT switching  | C <sub>L</sub> = 250 pF,                | V <sub>CC</sub> = 3 V to 4.5 V     | 1000 | -                  |     | kbit/s |  |
|   |                                    |                                     | C <sub>L</sub> = 1000 pF,               | V <sub>CC</sub> = 4.5 V to 5.5 V   | 1000 |                    |     |        |  |
| t <sub>sk(p)</sub>                        | Pulse skew <sup>(2)</sup>          | C <sub>L</sub> = 150 pF to 2500 pF, | $R_L = 3 k\Omega \text{ to } 7 k\Omega$ | See Figure 7-2                     |      | 300                |     | ns     |  |
|   | Slew rate                          | Slew rate, $R_L = 7 k\Omega$ ,      | $R_L = 7 k\Omega$ ,                     | C <sub>L</sub> = 150 pF to 1000 pl | F    | 8                  |     | 90     |  |
| SR(tr) transition region (see Figure 7-1) | transition region                  | D - 210                             | C <sub>L</sub> = 1000 pF                |                                    | 12   |                    | 60  | V/µs   |  |
|   | (see Figure 7-1)                   | $R_L = 3 k\Omega$                   | C <sub>L</sub> = 150 pF to 250 pF       |                                    | 24   |                    | 150 |        |  |

- All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.
- (2)
- Pulse skew is defined as  $|t_{PLH}-t_{PHL}|$  of each channel of the same device. Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V  $\pm$  0.5 V.

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#### 6.9 Electrical Characteristics: Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 9-1)

|                  | PARAMETER   | TEST CONDITIONS(2)                           | MIN                   | TYP <sup>(1)</sup>    | MAX | UNIT |
|------------------|---|--|-----------------------|-----------------------|-----|------|
| V <sub>OH</sub>  | High-level output voltage                               | I <sub>OH</sub> = -1 mA                      | V <sub>CC</sub> - 0.6 | V <sub>CC</sub> - 0.1 |     | V    |
| V <sub>OL</sub>  | Low-level output voltage                                | I <sub>OL</sub> = 1.6 mA                     |                       |                       | 0.4 | V    |
| V <sub>IT+</sub> | Positive-going input threshold voltage                  | V <sub>CC</sub> = 3.3 V                      |                       | 1.5                   | 2.4 | V    |
|                  | Positive-going input the should voltage                 | V <sub>CC</sub> = 5 V                        |                       | 1.8                   | 2.4 | V    |
| \/               | Negative-going input threshold voltage                  | V <sub>CC</sub> = 3.3 V                      | 0.6                   | 1.2                   |     | V    |
| $V_{IT-}$        | Negative-going input the shold voltage                  | V <sub>CC</sub> = 5 V                        | 0.8                   | 1.5                   |     | V    |
| V <sub>hys</sub> | Input hysteresis (V <sub>IT+</sub> – V <sub>IT-</sub> ) |  |                       | 0.3                   |     | V    |
| I <sub>OZ</sub>  | Output leakage current                                  | EN = 1                                       |                       | ±0.05                 | ±10 | μΑ   |
| r <sub>i</sub>   | Input resistance  | $V_1 = \pm 3 \text{ V to } \pm 25 \text{ V}$ | 3                     | 5                     | 7   | kΩ   |

All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

## **6.10 Switching Characteristics: Receiver**

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

|                    | PARAMETER   | TEST CONDITIONS(3)                                    | TYP <sup>(1)</sup> | UNIT |
|--------------------|---|---|--------------------|------|
| t <sub>PLH</sub>   | Propagation delay time, low- to high-level output | C <sub>L</sub> = 150 pF, See Figure 7-3               | 300                | ns   |
| t <sub>PHL</sub>   | Propagation delay time, high- to low-level output | C <sub>L</sub> = 150 pF, See Figure 7-3               | 300                | ns   |
| t <sub>en</sub>    | Output enable time                                | $C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 7-4 | 200                | ns   |
| t <sub>dis</sub>   | Output disable time                               | $C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 7-4 | 200                | ns   |
| t <sub>sk(p)</sub> | Pulse skew <sup>(2)</sup>                         | See Figure 7-3  | 300                | ns   |

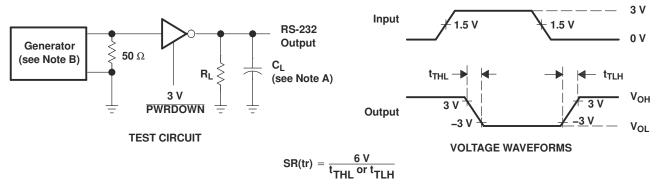
All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3  $V \pm 0.3$  V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5  $V \pm 0.5$  V.

Pulse skew is defined as  $|t_{PLH}-t_{PHL}|$  of each channel of the same device. Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V. (3)

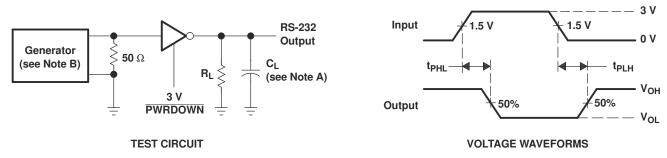


### 7 Parameter Measurement Information



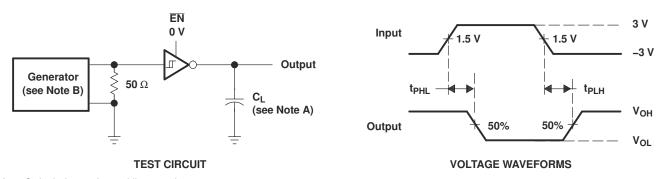
- A. C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 7-1. Driver Slew Rate



- C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

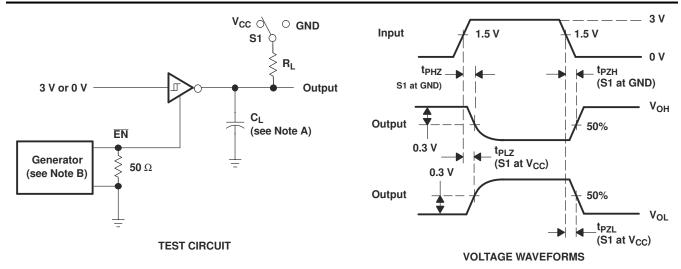
Figure 7-2. Driver Pulse Skew



- C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics:  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 7-3. Receiver Propagation Delay Times





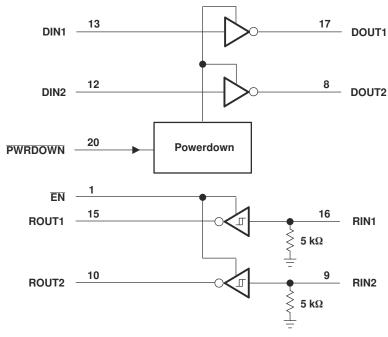
- A. C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics:  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 7-4. Receiver Enable and Disable Times



# **8 Detailed Description**

# 8.1 Functional Block Diagram



A. Pin numbers shown are for the DB, DW, and PW packages.

Figure 8-1. Logic Diagram (Positive Logic)

### 8.2 Device Functional Modes

Table 8-1. Function Table: Each Driver

| INP | UTS <sup>(1)</sup> | OUTPUT<br>DOUT |  |  |  |  |
|-----|--------------------|----------------|--|--|--|--|
| DIN | PWRDOWN            |                |  |  |  |  |
| Х   | L                  | Z              |  |  |  |  |
| L   | Н                  | Н              |  |  |  |  |
| Н   | Н                  | L              |  |  |  |  |

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Table 8-2. Function Table: Each Receiver

| INPUTS <sup>(1)</sup> |    | OUTPUT |  |  |  |  |
|-----------------------|----|--------|--|--|--|--|
| RIN                   | EN | ROUT   |  |  |  |  |
| L                     | L  | Н      |  |  |  |  |
| Н                     | L  | L      |  |  |  |  |
| X                     | Н  | Z      |  |  |  |  |
| Open                  | L  | Н      |  |  |  |  |

(1) H = high level, L = low level, X = irrelevant,Z = high impedance (off),

Open = input disconnected or connected driver off

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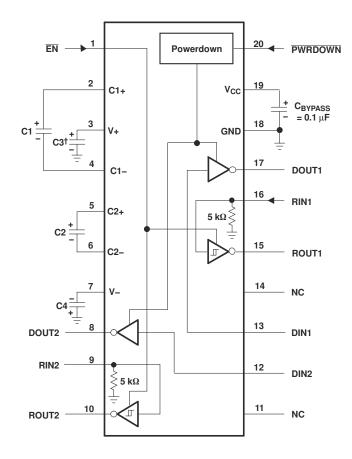
# 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 9.1 Application Information

## 9.2 Typical Application



 $<sup>^{\</sup>dagger}$  C3 can be connected to  $V_{CC}$  or GND.

NOTES: A. Resistor values shown are nominal.

#### V<sub>CC</sub> vs CAPACITOR VALUES

| V <sub>CC</sub>   | C1                    | C2, C3, and C4         |  |  |
|-------------------|-----------------------|------------------------|--|--|
| 3.3 V $\pm$ 0.3 V | <b>0.1</b> μ <b>F</b> | <b>0.1</b> μ <b>F</b>  |  |  |
| 5 V $\pm$ 0.5 V   | <b>0.047</b> μF       | <b>0.33</b> μ <b>F</b> |  |  |
| 3 V to 5.5 V      | <b>0.1</b> μ <b>F</b> | <b>0.47</b> μ <b>F</b> |  |  |

Figure 9-1. Typical Operating Circuit and Capacitor Values

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B. NC - No internal connection

C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.



# 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 10.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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## 10.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

# 10.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: TRSF3222E

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#### PACKAGING INFORMATION

| Orderable part number | Status | Material type | Package   Pins  | Package qty   Carrier | RoHS | Lead finish/    | MSL rating/        | Op temp (°C) | Part marking |
|-----------------------|--------|---------------|-----------------|-----------------------|------|-----------------|--------------------|--------------|--------------|
|                       | (1)    | (2)           |                 |                       | (3)  | Ball material   | Peak reflow        |              | (6)          |
|                       |        |               |                 |                       |      | (4)             | (5)                |              |              |
| TRSF3222ECDB          | Active | Production    | SSOP (DB)   20  | 70   TUBE             | Yes  | NIPDAU          | Level-1-260C-UNLIM | 0 to 70      | RT22EC       |
| TRSF3222ECDB.A        | Active | Production    | SSOP (DB)   20  | 70   TUBE             | Yes  | NIPDAU          | Level-1-260C-UNLIM | -40 to 85    | RT22EC       |
| TRSF3222EIDWR         | Active | Production    | SOIC (DW)   20  | 2000   LARGE T&R      | Yes  | NIPDAU          | Level-1-260C-UNLIM | -40 to 85    | TRSF3222EI   |
| TRSF3222EIDWR.A       | Active | Production    | SOIC (DW)   20  | 2000   LARGE T&R      | Yes  | NIPDAU          | Level-1-260C-UNLIM | -40 to 85    | TRSF3222EI   |
| TRSF3222EIPWR         | Active | Production    | TSSOP (PW)   20 | 2000   LARGE T&R      | Yes  | NIPDAU   NIPDAU | Level-1-260C-UNLIM | -40 to 85    | RT22EI       |
| TRSF3222EIPWR.A       | Active | Production    | TSSOP (PW)   20 | 2000   LARGE T&R      | Yes  | NIPDAU          | Level-1-260C-UNLIM | -40 to 85    | RT22EI       |
| TRSF3222EIPWRG4       | Active | Production    | TSSOP (PW)   20 | 2000   LARGE T&R      | Yes  | NIPDAU   NIPDAU | Level-1-260C-UNLIM | -40 to 85    | RT22EI       |
| TRSF3222EIPWRG4.A     | Active | Production    | TSSOP (PW)   20 | 2000   LARGE T&R      | Yes  | NIPDAU          | Level-1-260C-UNLIM | -40 to 85    | RT22EI       |

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE OPTION ADDENDUM**

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width     |
|----|---|
| В0 | Dimension designed to accommodate the component length    |
| K0 | Dimension designed to accommodate the component thickness |
| W  | Overall width of the carrier tape                         |
| P1 | Pitch between successive cavity centers                   |

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

| Device          | Package<br>Type | Package<br>Drawing |    | SPQ  | Reel<br>Diameter<br>(mm) | Reel<br>Width<br>W1 (mm) | A0<br>(mm) | B0<br>(mm) | K0<br>(mm) | P1<br>(mm) | W<br>(mm) | Pin1<br>Quadrant |
|-----------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TRSF3222EIDWR   | SOIC            | DW                 | 20 | 2000 | 330.0                    | 24.4                     | 10.8       | 13.3       | 2.7        | 12.0       | 24.0      | Q1               |
| TRSF3222EIPWR   | TSSOP           | PW                 | 20 | 2000 | 330.0                    | 16.4                     | 6.95       | 7.0        | 1.4        | 8.0        | 16.0      | Q1               |
| TRSF3222EIPWR   | TSSOP           | PW                 | 20 | 2000 | 330.0                    | 16.4                     | 6.95       | 7.0        | 1.4        | 8.0        | 16.0      | Q1               |
| TRSF3222EIPWRG4 | TSSOP           | PW                 | 20 | 2000 | 330.0                    | 16.4                     | 6.95       | 7.1        | 1.6        | 8.0        | 16.0      | Q1               |
| TRSF3222EIPWRG4 | TSSOP           | PW                 | 20 | 2000 | 330.0                    | 16.4                     | 6.95       | 7.0        | 1.4        | 8.0        | 16.0      | Q1               |



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#### \*All dimensions are nominal

| Device          | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|-----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TRSF3222EIDWR   | SOIC         | DW              | 20   | 2000 | 367.0       | 367.0      | 45.0        |
| TRSF3222EIPWR   | TSSOP        | PW              | 20   | 2000 | 356.0       | 356.0      | 35.0        |
| TRSF3222EIPWR   | TSSOP        | PW              | 20   | 2000 | 356.0       | 356.0      | 35.0        |
| TRSF3222EIPWRG4 | TSSOP        | PW              | 20   | 2000 | 356.0       | 356.0      | 35.0        |
| TRSF3222EIPWRG4 | TSSOP        | PW              | 20   | 2000 | 356.0       | 356.0      | 35.0        |

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



#### \*All dimensions are nominal

|   | Device         | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|---|----------------|--------------|--------------|------|-----|--------|--------|--------|--------|
|   | TRSF3222ECDB   | DB           | SSOP         | 20   | 70  | 530    | 10.5   | 4000   | 4.1    |
| Γ | TRSF3222ECDB.A | DB           | SSOP         | 20   | 70  | 530    | 10.5   | 4000   | 4.1    |





#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SOIC



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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